

DUAL DMOS FULL BRIDGE MOTOR DRIVER

PRELIMINARY DATA

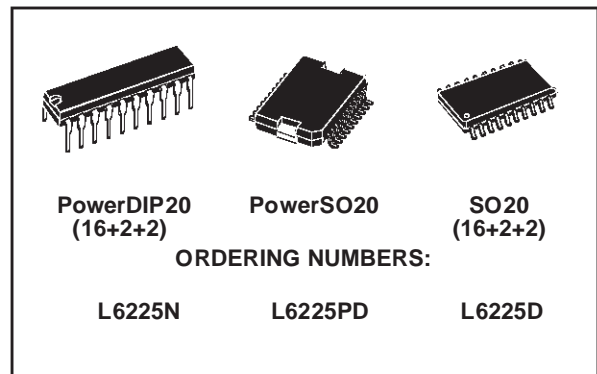
- OPERATING SUPPLY VOLTAGE FROM 8 TO 52V
- 2.8A PEAK CURRENT (1.4A DC)
- $R_{DS(ON)}$ 0.73 Ω TYP. VALUE @ $T_j = 25^\circ\text{C}$
- CROSS CONDUCTION PROTECTION
- THERMAL SHUTDOWN
- OPERATING FREQUENCY UP TO 100KHz
- HIGH SIDE OVER CURRENT PROTECTION
- CMOS/TTL INPUT
- INTRINSIC FAST FREE WHEELING DIODES
- UNDER VOLTAGE LOCKOUT

TYPICAL APPLICATIONS

- STEPPER MOTOR
- DUAL OR QUAD DC MOTOR

DESCRIPTION

The L6225 is a dual full bridge driver for motor control applications manufactured with Multipower BCD technology which combines isolated DMOS power



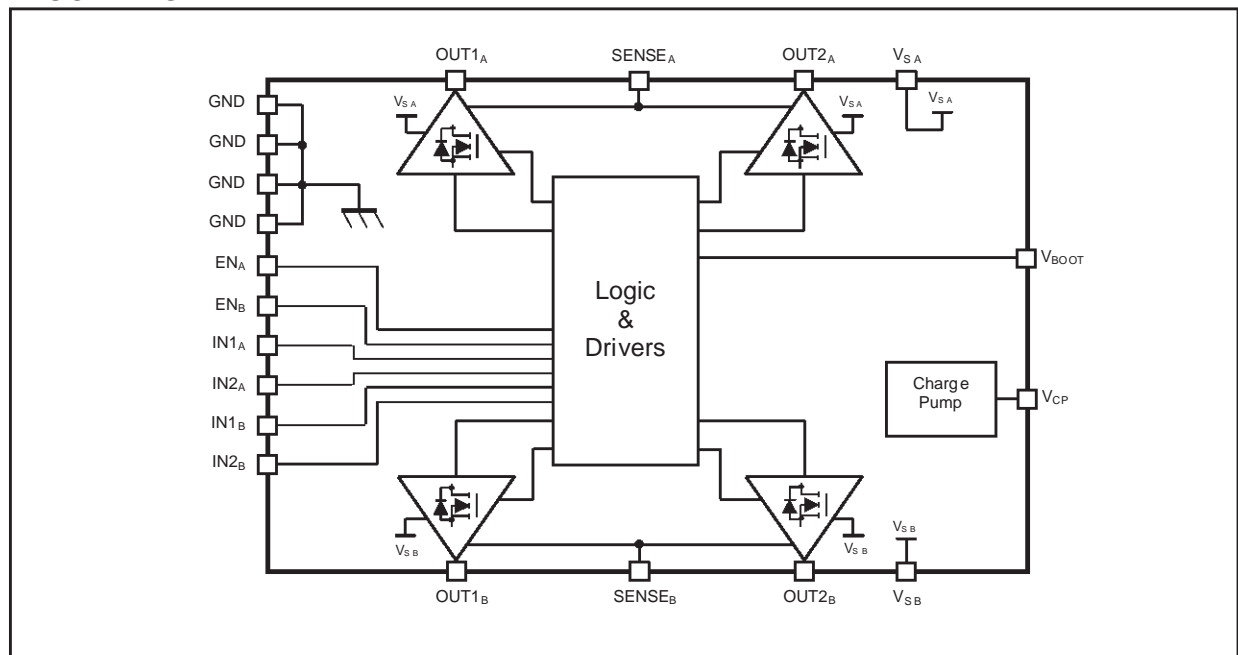
transistors with CMOS and bipolar circuits on the same chip.

The Logic Inputs are CMOS/TTL and μP compatible. The High Side switches are protected against unsafe over current conditions.

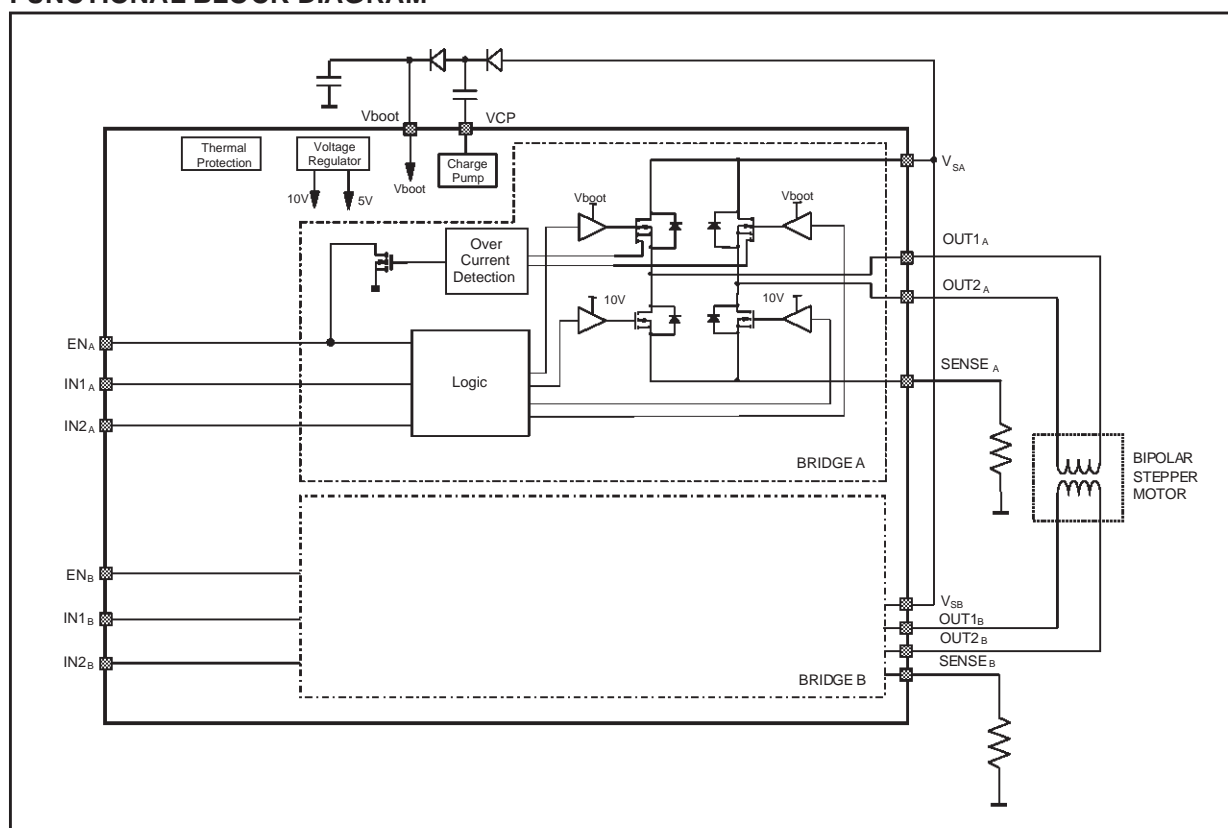
Each full bridge is controlled by a separate Enable and has a sense pin for the current sense resistor insertion. Another feature is the thermal shutdown.

The L6225 is assembled in PowerDIP20(16+2+2), PowerSO20 and SO20(16+2+2) packages.

BLOCK DIAGRAM



FUNCTIONAL BLOCK DIAGRAM



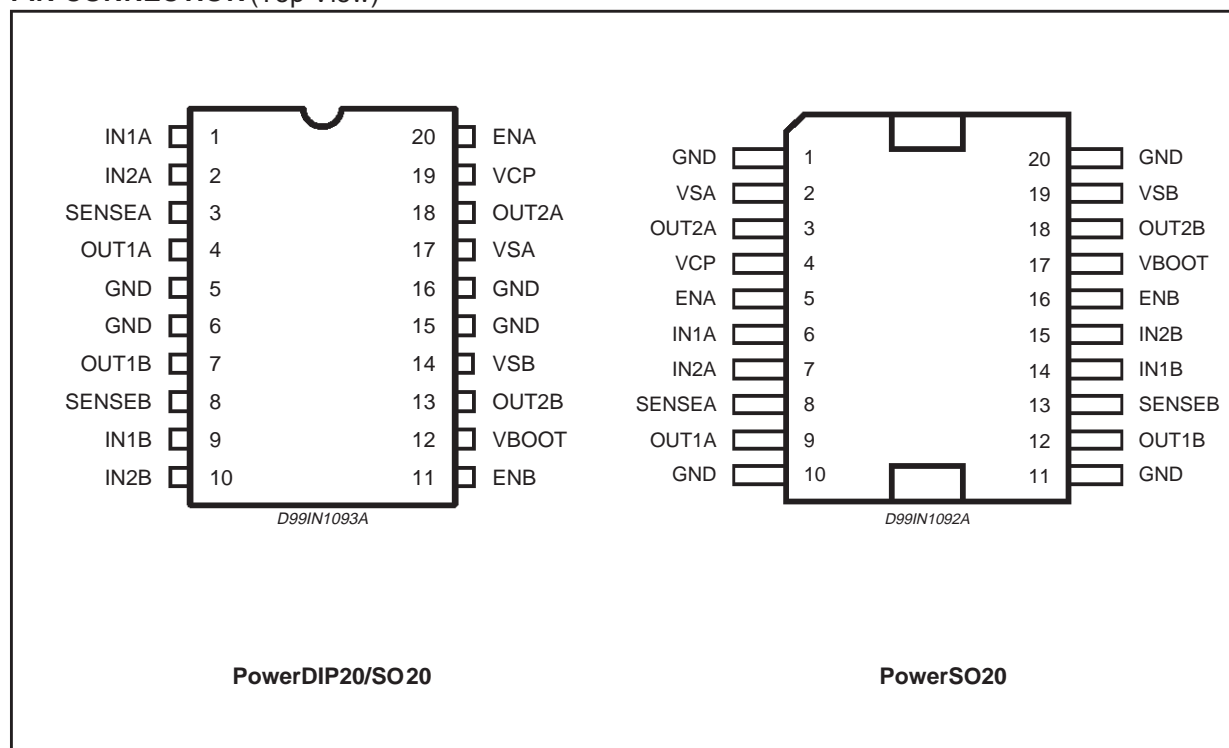
ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Test conditions	Value	Unit
V_S	Supply Voltage		60	V
V_{IN}, V_{EN}	Input and Enable Voltage Range		-0.3 to +7	V
V_{SENSE}	DC Sensing Voltage Range		-1 to +4	V
V_{BOOT}	Bootstrap Peak Voltage		$V_S + 10$	V
$I_{S(peak)}$	Pulsed Supply Current (for each V_S pin), internally limited by the overcurrent protection	$t_{PULSE} < 1ms$	3.55	A
I_S	DC Supply Current (for each V_S pin)		1.4	A
V_{OD}	Differential Voltage Between V_{SA} , $OUT1_A$, $OUT2_A$, $SENSE_A$ and V_{SB} , $OUT1_B$, $OUT2_B$, $SENSE_B$		60	V
T_{stg}, T_{OP}	Storage and Operating Temperature Range		-40 to 150	°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	MIN	MAX	Unit
V_S	Supply Voltage	12	52	V
V_{OD}	Differential Voltage Between $V_{S\ A}$, $OUT1_A$, $OUT2_A$, $SENSE_A$ and $V_{S\ B}$, $OUT1_B$, $OUT2_B$, $SENSE_B$		52	V
V_{SENSE}	Sensing voltage (pulsed $tw < t_{rr}$) (DC)	-6 -1	6 1	V V
V_{ref}	V_{ref} Operating Voltage	-0.1	5	V
I_{OUT}	DC Output Current		1.4	A
T_j	Operating Junction Temperature	-25	+125	°C
f_{sw}	Switching Frequency		100	kHz

PIN CONNECTION (Top View)



PIN DESCRIPTION

Name	PowerSO20	PowerDIP20/ SO20	Function
V _{SA}	2	17	Supply Voltage of the Bridge A.
V _{SB}	19	14	Supply Voltage of the Bridge B. This pin must be connected to V _{SA} .
OUT1 _A OUT2 _A	9 3	4 18	Bridge A outputs.
OUT1 _B OUT2 _B	12 18	7 13	Bridge B outputs.
SENSE _A	8	3	Sense resistor for the bridge A
SENSE _B	13	8	Sense resistor for the bridge B
GND	1,10,11,20	5, 6,15,16	Common ground terminals. In Powerdip and SO packages, these pins are also used for heat dissipation toward the PCB.
EN _A	5	20	Enable of the Bridge A. A LOW logic level applied to this pin switches off all the power DMOSs of the related bridge. The Bridge A over current protection open drain is internally connected to this pin.
EN _B	16	11	Enable of the Bridge B. A LOW logic level applied to this pin switches off all the power DMOSs of the related bridge. The Bridge B over current protection open drain is internally connected to this pin.
IN1 _A IN2 _A	6 7	1 2	Logic inputs of the Bridge B. Provided the ENA signal is HIGH, a HIGH logic level applied to any of these pins switches on the related high side power DMOS, while a logic LOW switches on the related low side power DMOS.
IN1 _B IN2 _B	14 15	9 10	Logic inputs of the Bridge B. Provided the ENB signal is HIGH, a HIGH logic level applied to any of these pins switches on the related high side power DMOS, while a logic LOW switches on the related low side power DMOS.
V _{CP}	4	19	Bootstrap Oscillator. Oscillator output for the external charge pump.
V _{BOOT}	17	12	Supply voltage to overdrive the upper DMOSs.

THERMAL DATA

Symbol	Description	PowerDIP20	SO20	PowerSO20	Unit
R _{th-j-pins}	Maximum Thermal Resistance Junction-Pins	13	15	-	°C/W
R _{th-j-case}	Maximum Thermal Resistance Junction-Case	-	-	2	°C/W
R _{th-j-amb1}	Maximum Thermal Resistance Junction-Ambient ⁽¹⁾	41	51	-	°C/W
R _{th-j-amb1}	Maximum Thermal Resistance Junction-Ambient ⁽²⁾	-	-	36	°C/W
R _{th-j-amb1}	Maximum Thermal Resistance Junction-Ambient ⁽³⁾	-	-	16	°C/W
R _{th-j-amb2}	Maximum Thermal Resistance Junction-Ambient ⁽⁴⁾	57	78	63	°C/W

(1) Mounted on a multilayer FR4 PCB with a dissipating copper surface on the bottom side of 6 cm² (with a thickness of 35 μm).

(2) Mounted on a multilayer FR4 PCB with a dissipating copper surface on the top side of 6 cm² (with a thickness of 35 μm).

(3) Mounted on a multilayer FR4 PCB with a dissipating copper surface on the top side of 6 cm² (with a thickness of 35 μm), 16 via holes and a ground layer.

(4) Mounted on a multilayer PCB without any heatsinking surface on the board.

ELECTRICAL CHARACTERISTICS($T_{amb} = 25\text{ }^{\circ}\text{C}$, $V_S = 48\text{V}$, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_S	Supply Voltage		8		52	V
I_S	Quiescent Supply Current	All Bridges OFF; $-25^{\circ}\text{C} < T_J < 125^{\circ}\text{C}$		5.5	10	mA
T_J	Thermal Shutdown Temperature		150			$^{\circ}\text{C}$

Output DMOS Transistors

I_{DSS}	Leakage Current	$V_S = 52\text{V}$			1	mA
$R_{DS(ON)}$	High-side + Low-side Switch ON Resistance	$T_J = 25^{\circ}\text{C}$		1.47	1.69	Ω
		$T_J = 125^{\circ}\text{C}$		2.35	2.7	Ω

Source Drain Diodes

V_{SD}	Forward ON Voltage	$I_{SD} = 1.4\text{A}$, EN = LOW			1.2	V
t_{rr}	Reverse Recovery Time	$I_f = 1.4\text{A}$		300		ns
t_{fr}	Forward Recovery Time			200		ns

Switching Rates

$t_{D(ON)EN}$	Enable to out turn ON delay time ⁽⁵⁾	$I_{LOAD} = 1.4\text{ A}$		250		ns
$t_{D(ON)IN}$	Input to out turn ON delay time ⁽⁵⁾			600		ns
t_{ON}	Output rise time ⁽⁵⁾		20	105	300	ns
$t_{D(OFF)EN}$	Enable to out turn OFF delay time ⁽⁵⁾			450		ns
$t_{D(OFF)IN}$	Input to out turn OFF delay time ⁽⁵⁾			500		ns
t_{off}	Output fall time ⁽⁵⁾		20	78	300	ns
t_{dt}	Dead time protection			1		μs
f_{CP}	Charge pump frequency			0.75	1	MHz

UVLO comp

$V_{th(ON)}$	Turn ON threshold		6.6	7	7.4	V
$V_{th(OFF)}$	Turn OFF threshold		5.6	6	6.4	V

Logic Input

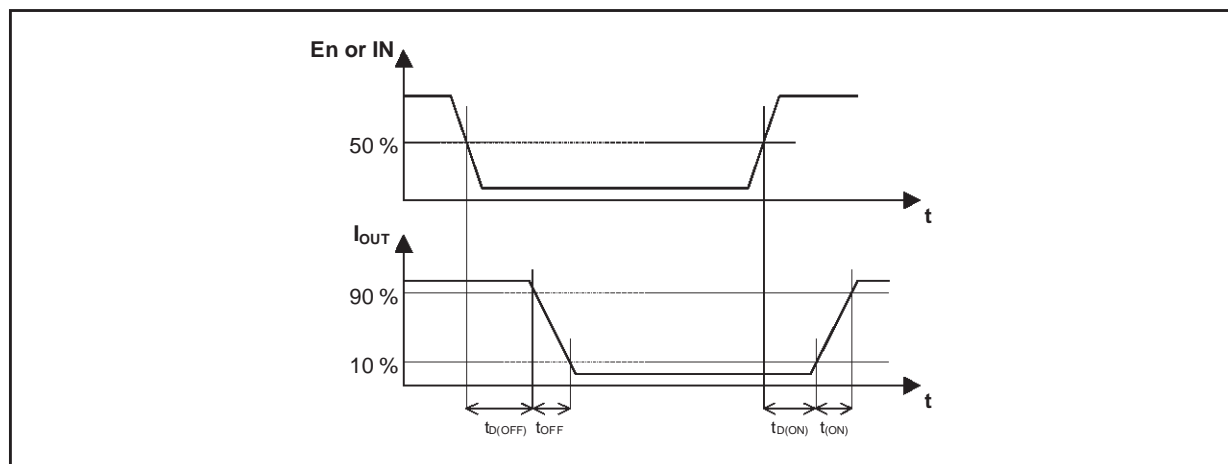
V_{INL}	Low level logic input voltage		-0.3		0.8	V
V_{INH}	High level logic input voltage		2		7	V
I_{INH}	High level logic input current	$V_{IN, EN} = 5\text{ V}$			70	μA
I_{INL}	Low level logic input current	$V_{IN, EN} = \text{GND}$			-10	μA

Over Current Protection

$I_{S\text{ OVER}}$	Input supply over current protection threshold		2	2.8	3.55	A
V_{DIAG}	Open drain low level output voltage	$I = 4\text{ mA}$			0.4	V

(5) Resistive load used. See Fig. 1.

Figure 1. Switching rates definition



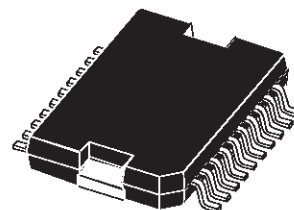
CIRCUIT DESCRIPTION

The L6225 is a dual full bridge IC designed to drive DC or stepper motors and other inductive loads. Each bridge has 4 power DMOS transistors with a typical $R_{DS(ON)}$ of 0.3 Ohm. Any of the 4 half bridges can be controlled independently by means of the 4 TTL/CMOS compatible inputs $IN1_A$, $IN2_A$, $IN1_B$, $IN2_B$, and 2 enable ENA , ENB . External connections are provided so that sensing resistor can be added for constant current chopping application. A non dissipative current sensing on the supply rails of the high side power DMOSs of each bridge, an internal reference and an internal open drain, with a pull down capability of 4mA (typical value), will pull to GND the EN - $ABLE$ pin of the bridge under fault conditions, turning OFF all the four PowerDMOSs. This ensures a protection against short circuit to GND and between two phases of each of the two independent full bridges. By using an external R-C on the EN pins, the off time before recovering normal operation conditions after a fault can be easily programmed, by means of the accurate threshold of the logic inputs. Note that protection against short to the supply rail is typically provided by the external current control circuitry. The trip point of this protection is set at 2.8A (typ value).

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			3.6			0.142
a1	0.1		0.3	0.004		0.012
a2			3.3			0.130
a3	0		0.1	0.000		0.004
b	0.4		0.53	0.016		0.021
c	0.23		0.32	0.009		0.013
D (1)	15.8		16	0.622		0.630
D1	9.4		9.8	0.370		0.386
E	13.9		14.5	0.547		0.570
e		1.27			0.050	
e3		11.43			0.450	
E1 (1)	10.9		11.1	0.429		0.437
E2			2.9			0.114
E3	5.8		6.2	0.228		0.244
G	0		0.1	0.000		0.004
H	15.5		15.9	0.610		0.626
h			1.1			0.043
L	0.8		1.1	0.031		0.043
N	10° (max.)					
S	8° (max.)					
T		10			0.394	

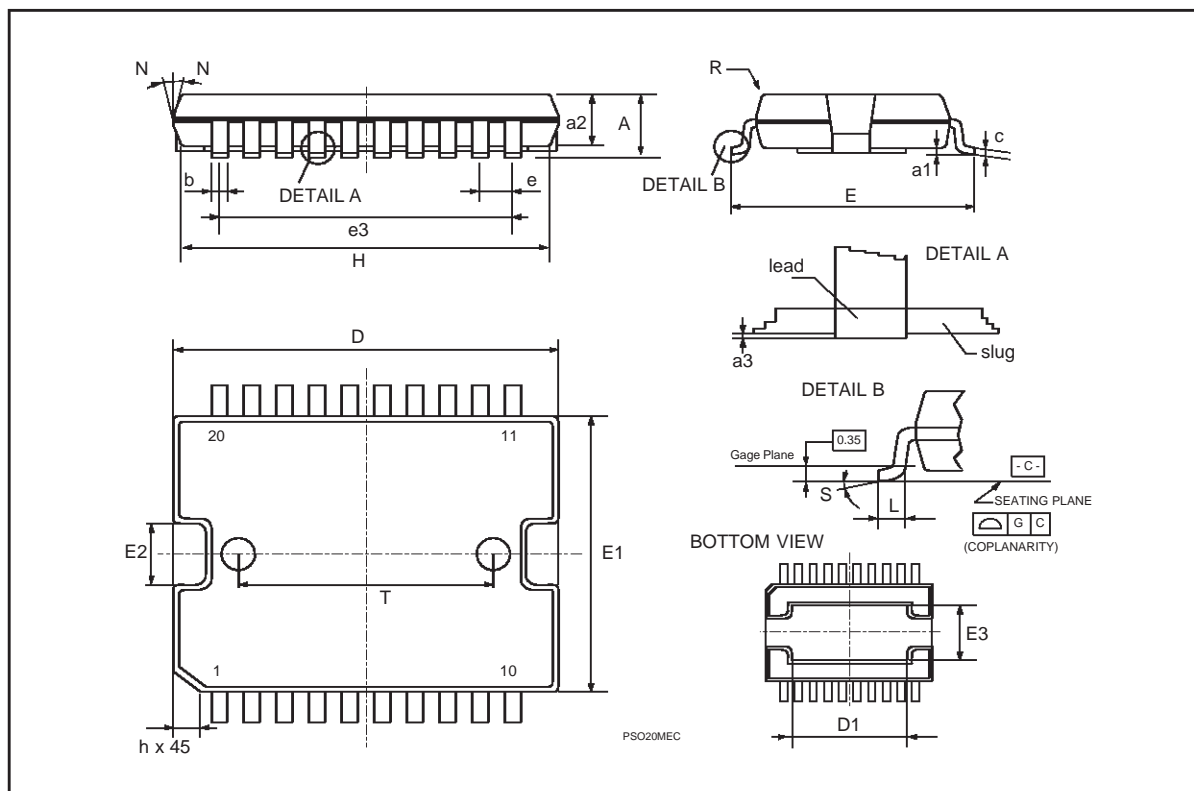
(1) "D and F" do not include mold flash or protrusions.
- Mold flash or protrusions shall not exceed 0.15 mm (0.006").
- Critical dimensions: "E", "G" and "a3"

OUTLINE AND MECHANICAL DATA



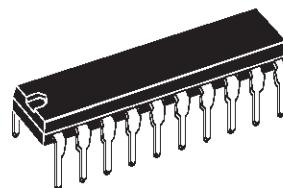
JEDEC MO-166

PowerSO20

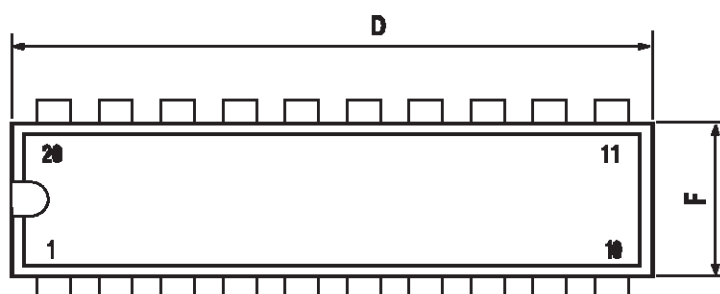
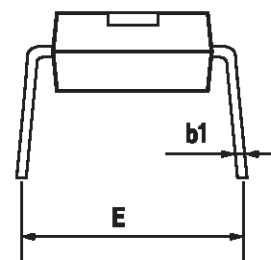
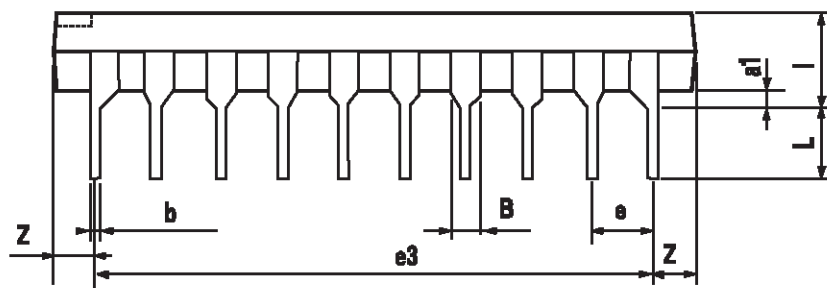


DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.85		1.40	0.033		0.055
b		0.50			0.020	
b1	0.38		0.50	0.015		0.020
D			24.80			0.976
E		8.80			0.346	
e		2.54			0.100	
e3		22.86			0.900	
F			7.10			0.280
I			5.10			0.201
L		3.30			0.130	
Z			1.27			0.050

OUTLINE AND MECHANICAL DATA

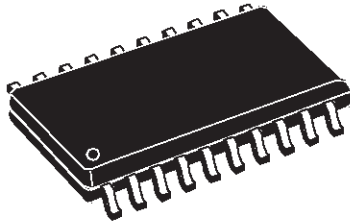


Powerdip 20

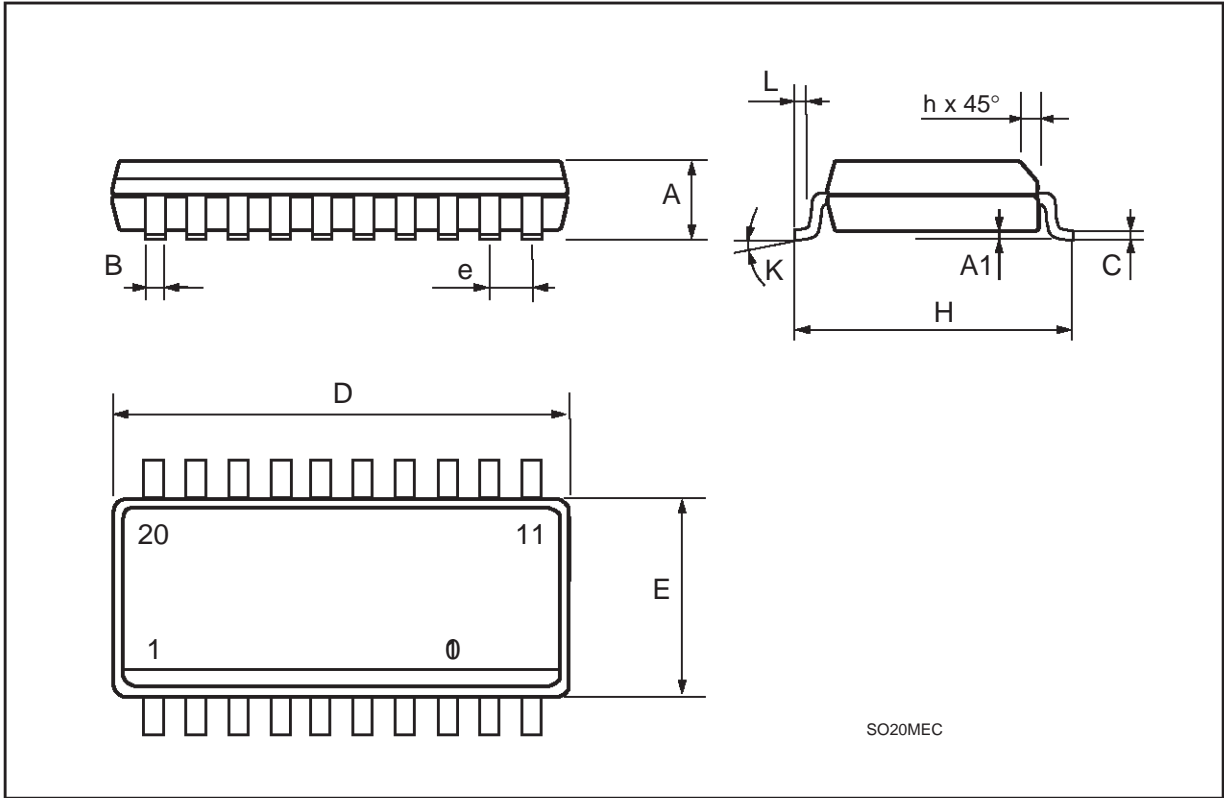


DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.35		2.65	0.093		0.104
A1	0.1		0.3	0.004		0.012
B	0.33		0.51	0.013		0.020
C	0.23		0.32	0.009		0.013
D	12.6		13	0.496		0.512
E	7.4		7.6	0.291		0.299
e		1.27			0.050	
H	10		10.65	0.394		0.419
h	0.25		0.75	0.010		0.030
L	0.4		1.27	0.016		0.050
K	0° (min.)8° (max.)					

**OUTLINE AND
MECHANICAL DATA**



SO20



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